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(54) **CHIP PACKAGE STRUCTURE AND
MANUFACTURING METHOD THEREOF**

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H01L 23/49503 (2013.01); **H01L 23/49524**
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2924/181; H01L 2224/48091; H01L
2224/73265; H01L 23/495; H01L 33/00;
H01L 31/12; H01L 21/4814; H01S 5/02244;
H01S 5/02248; B81B 2207/09; B81B 7/0032;
B81C 1/0023; B81C 1/00238; B81C 1/00246;
B81C 1/00253; B81C 1/00261; B81C
1/00269

See application file for complete search history.

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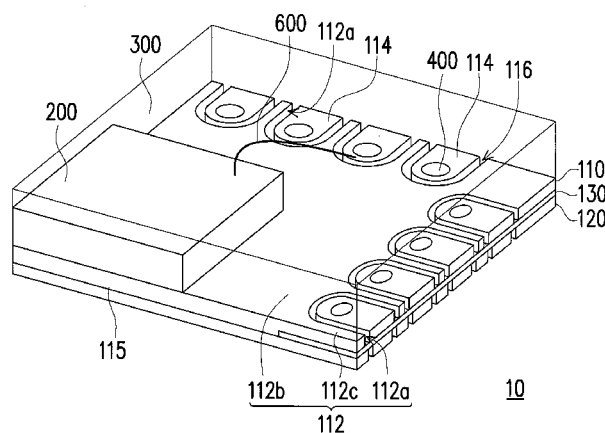
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(57)

ABSTRACT

A chip package structure includes a lead frame having first and second patterned metal layers and an insulation layer, a chip, and an encapsulant covering the first patterned metal layer and the chip. The first patterned metal layer includes a chip pad with first recesses and bonding pads in the first recesses. A first groove exists between each bonding pad and the chip pad. The second patterned metal layer connecting the first patterned metal layer includes terminal pads and a heat dissipation block thermally coupled to the chip pad. The heat dissipation block includes second recesses where the terminal pads are located and electrically connected to the corresponding bonding pads. A second groove exists between each terminal pad and the heat dissipation block. The insulation layer is located between the bonding pads and the terminal pads. The chip on the chip pad is electrically connected to the bonding pads.

9 Claims, 5 Drawing Sheets



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FIG. 1A

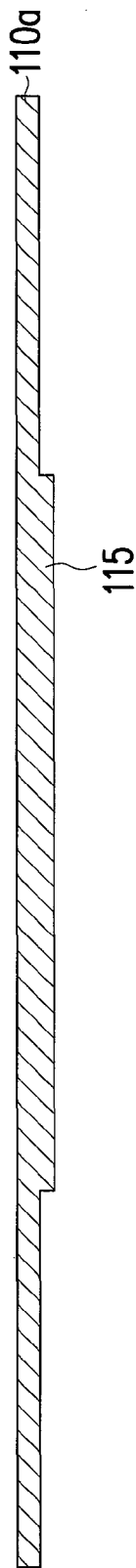


FIG. 1B

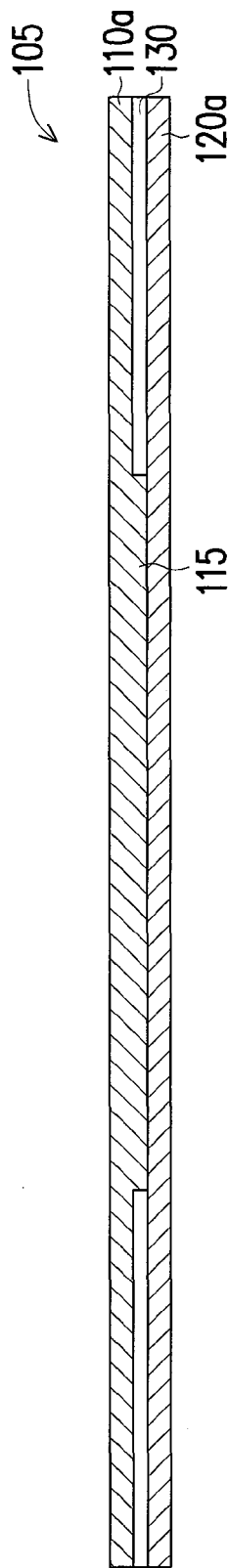


FIG. 1C

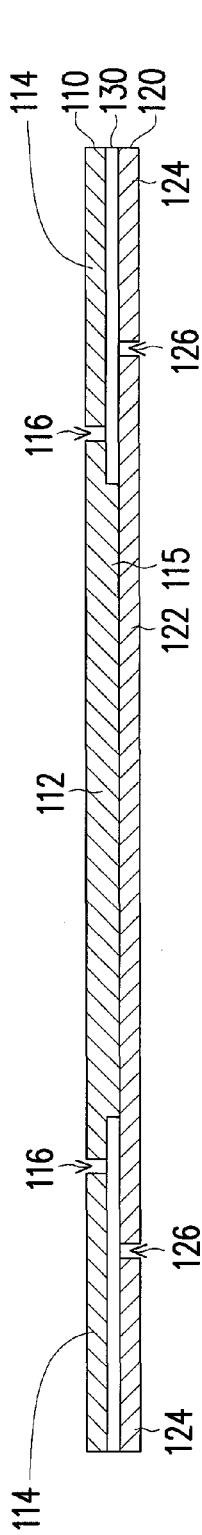


FIG. 1D

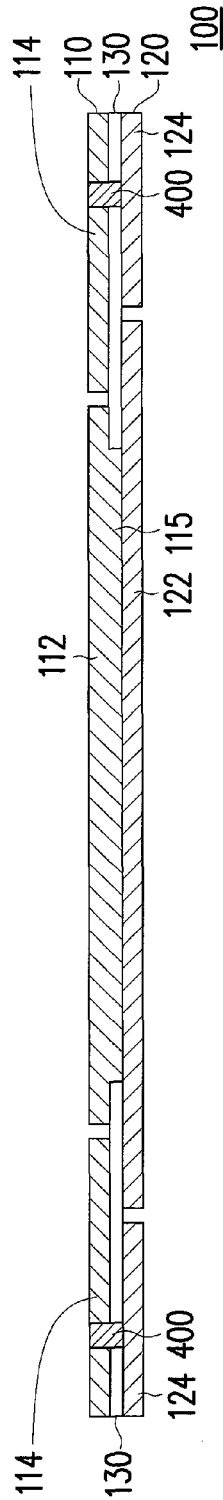


FIG. 1E

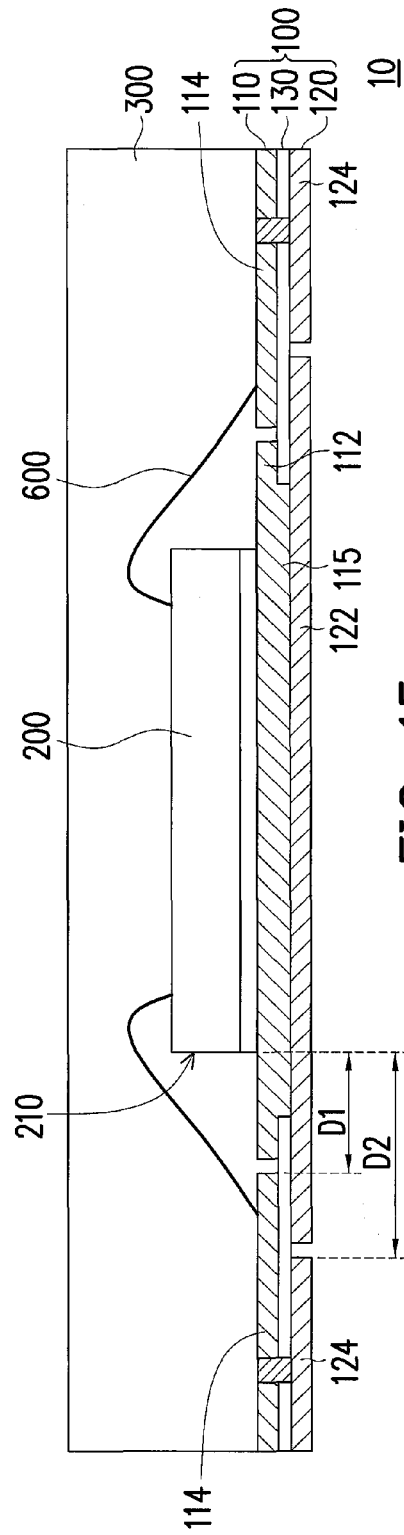


FIG. 1F

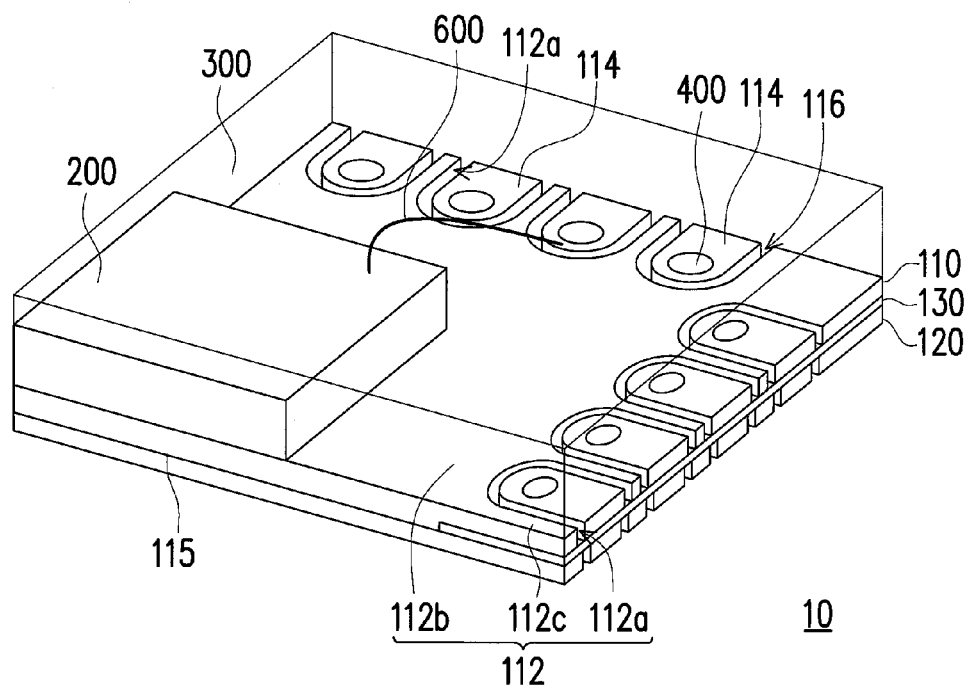


FIG. 2

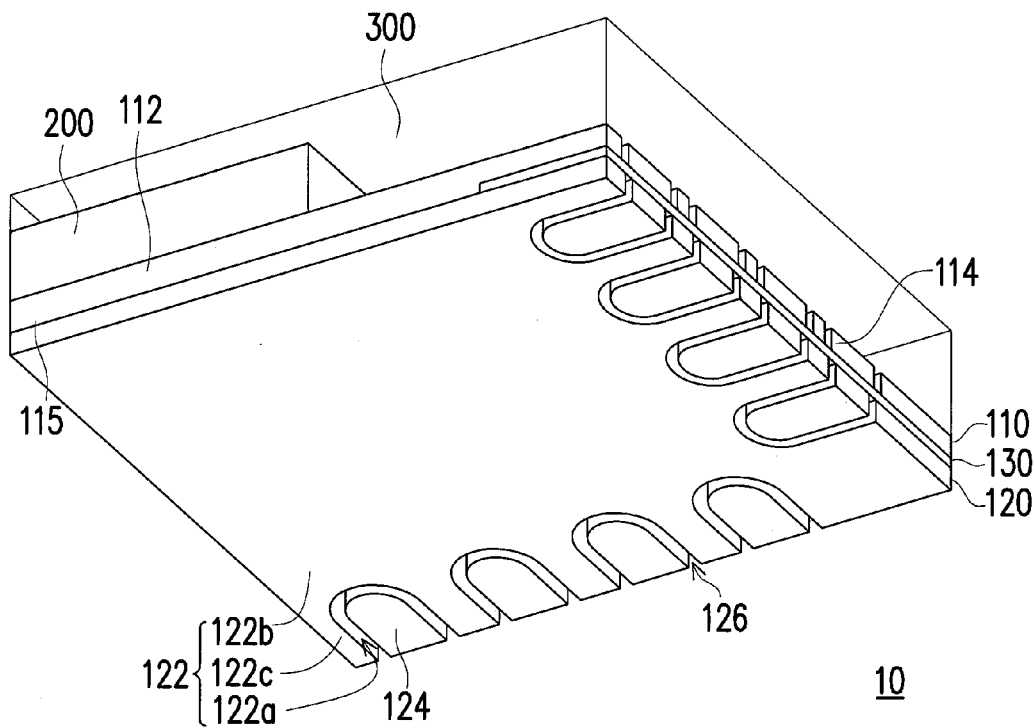


FIG. 3

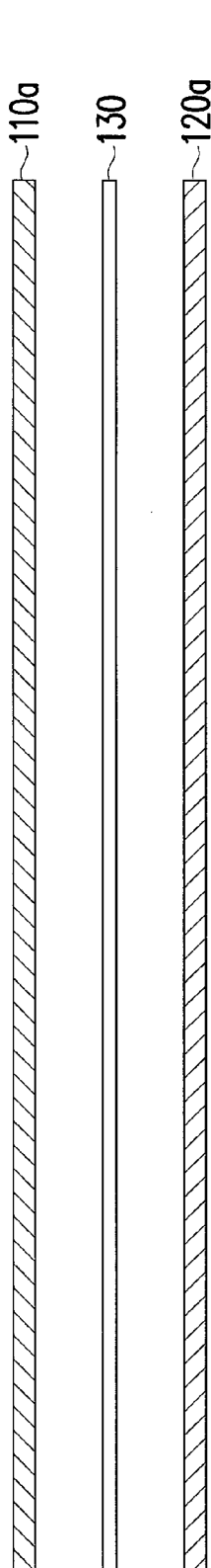


FIG. 4A

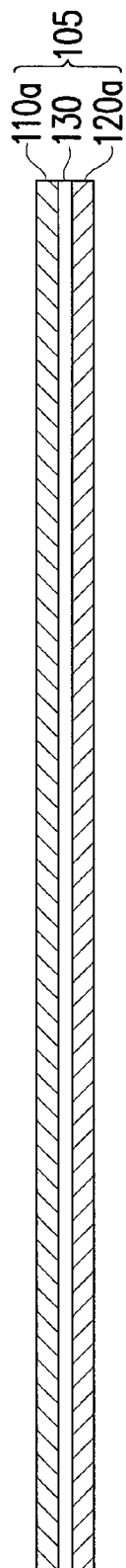


FIG. 4B

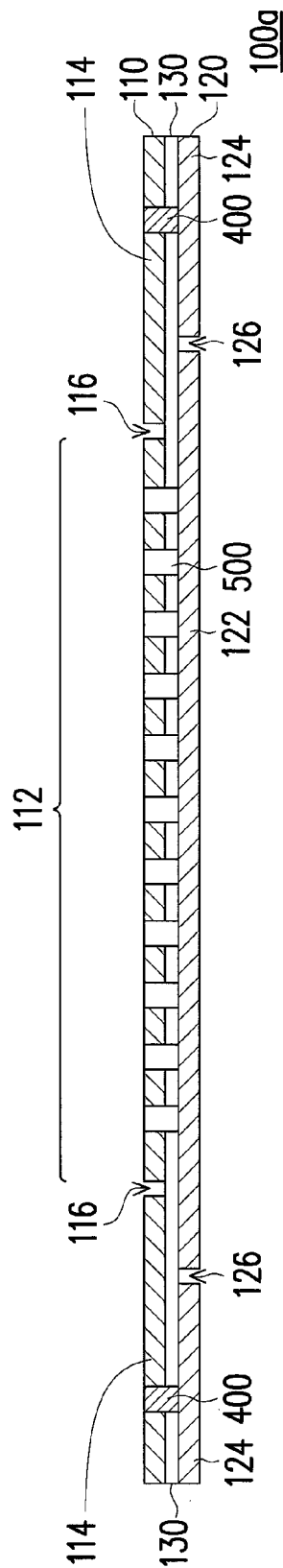


FIG. 4C

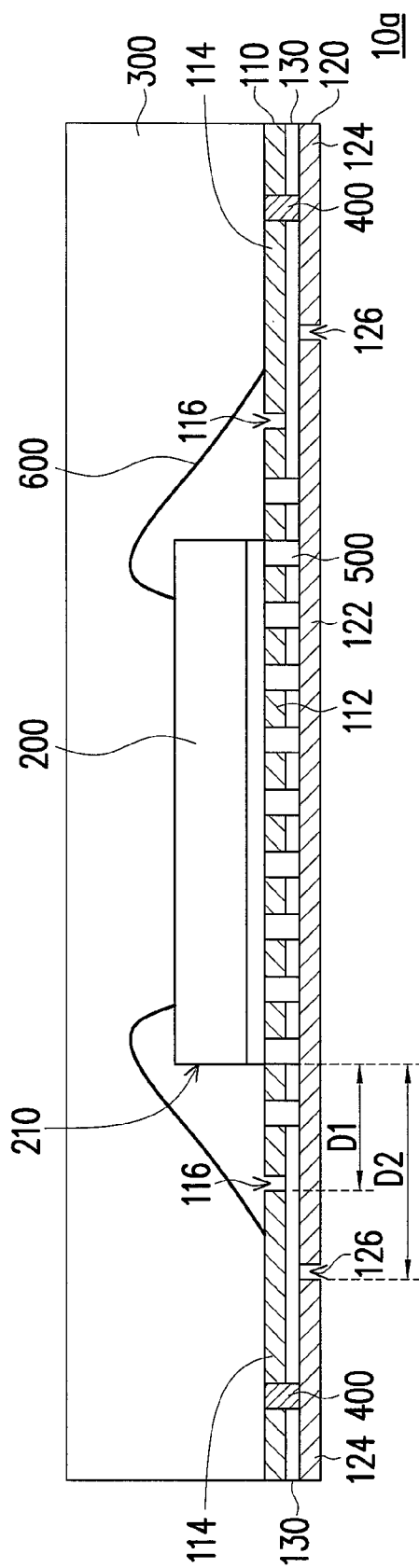


FIG. 4D

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CHIP PACKAGE STRUCTURE AND MANUFACTURING METHOD THEREOF

CROSS-REFERENCE TO RELATED APPLICATION

This application claims the priority benefit of Taiwan application serial no. 103112581, filed on Apr. 3, 2014. The entirety of the above-mentioned patent application is hereby incorporated by reference herein and made a part of this specification.

BACKGROUND OF THE INVENTION

1. Field of the Invention

The invention relates to a semiconductor package structure and a manufacturing method thereof; more particularly, the invention relates to a chip package structure and a manufacturing method thereof.

2. Description of Related Art

In regard to the wire bonding technology, a lead-frame based design is mostly applied to the low pin-count IC packages. After going through the processes of wafer sawing, die bonding, wire bonding, molding, and trimming/forming, a conventional lead-frame based chip package is substantially completed.

To comply with the trend of lightness, slimness, shortness, and compactness of modern electronic devices, the sizes of chips also tend toward miniaturization accordingly. As the chip size is reduced, the distance between the chip and the inner leads of the lead frame is increased, and the lengths of the bonding wires for electrically connecting the chip to the inner leads of the lead frame have to be lengthened. However, when the lengths and the loop angles of the bonding wires are increased, the bonding wires are likely to collapse causing short circuit, and likely to be broken by the molding compound during molding injection process resulting in open circuit, both of which would reduce the yield rate of the chip packages. Besides, re-fabrication of the molds for producing the lead frames adapted to miniaturized chips would increase the overall production cost.

Furthermore, with the increasing integration density, chips become more and more complicated and multi-functional, and thus heat generated during the operation of the chips keeps increasing. Generally, the heat generated by the chip being dissipated directly through the chip pad has the best heat dissipation effect. Nevertheless, the chip pad and the leads of the conventional lead frame need be completely electrically insulated, and thus the chip pad and the leads should be separated by certain spacing, which poses a limitation to the size of the chip pad. Thus, the heat dissipation area of the chip pad cannot be effectively expanded so that the heat generated by the chip cannot be effectively dissipated, and the heat dissipation efficiency of the chip package structure is reduced.

SUMMARY OF THE INVENTION

The invention is directed to a chip package structure and a manufacturing method thereof, which are able to reduce the distance of wire bonding and enhance the heat dissipation efficiency.

In an embodiment, a chip package structure that includes a lead frame, a chip, and an encapsulant is provided. The lead frame includes a first patterned metal layer, a second patterned metal layer, and an insulation layer. The first patterned metal layer includes a chip pad and a plurality of

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bonding pads. The chip pad includes a plurality of first recesses. The first recesses are located at a periphery of the chip pad. The bonding pads are respectively located in the first recesses, and a first groove exists between each of the bonding pads and the chip pad. The second patterned metal layer is connected to the first patterned metal layer and includes a plurality of terminal pads and a heat dissipation block. The heat dissipation block is thermally coupled to the chip pad and includes a plurality of second recesses. The second recesses are located at a periphery of the heat dissipation block. The terminal pads are respectively located in the second recesses and electrically connected to the corresponding bonding pads. A second groove exists between each of the terminal pads and the heat dissipation block. The insulation layer is located between the bonding pads and the terminal pads. The chip is disposed on the chip pad and electrically connected to the bonding pads. The encapsulant covers the first patterned metal layer and the chip.

In an embodiment of the invention, a manufacturing method of a chip package structure includes following steps. A substrate is provided. The substrate includes a first metal layer, a second metal layer, and an insulation layer located between the first metal layer and the second metal layer. A first groove is formed in the first metal layer to form a first patterned metal layer. The first patterned metal layer includes a chip pad and a plurality of bonding pads, and the first groove exists between each of the bonding pads and the chip pad. The chip pad includes a plurality of first recesses located at a periphery of the chip pad. The bonding pads are respectively located in the first recesses. A second groove is formed in the second metal layer to form a second patterned metal layer. The second patterned metal layer includes a heat dissipation block and a plurality of terminal pads, and the second groove exists between each of the terminal pads and the heat dissipation block. The heat dissipation block includes a plurality of second recesses located at a periphery of the heat dissipation block. The terminal pads are respectively located in the second recesses, and the heat dissipation block is thermally coupled to the chip pad. Plural conductive vias are formed. The conductive vias respectively penetrate the bonding pads and the insulation layer and are connected to the corresponding terminal pads so as to electrically connect the bonding pads with the terminal pads. A chip is disposed on the chip pad and electrically connected to the bonding pads. An encapsulant is formed. The encapsulant covers the first patterned metal layer and the chip.

In view of the above, the chip package structure in the invention is formed by forming the first groove in the first metal layer of the substrate to separate the chip pad from the bonding pads, and forming the second groove in the second metal layer of the substrate to separate the heat dissipation block from the terminal pads. Thus, the bonding pads can extend near to the periphery of the chip according to product requirements, so as to reduce the distance of wire bonding. Thereby, the material cost can be reduced, and the yield of the wire bonding process and the subsequent processes can be improved. Besides, the dimensions of the terminal pads need not be equal to the dimensions of the corresponding bonding pads and may be properly reduced according to actual product requirements so that the dimensions of the heat dissipation block can be enlarged and the resultant heat dissipation area of the heat dissipation block is increased.

In addition, since the chip pad formed according to the manufacturing method described herein extends between the adjacent bonding pads, and the heat dissipation block extends between the adjacent terminal pads, not only the

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heat dissipation area is increased, but also the distance between the heat dissipation region and the electrical connection region is shortened so that the thermal impedance of the chip package structure is reduced. Moreover, since the first patterned metal layer and the second patterned metal layer described herein are insulated from each other by the insulation layer, during the molding process, the encapsulant is unable to overflow onto the bottom surface of the second patterned metal layer through the first groove and the second groove, so that it is not necessary to adhere a tape to the bottom surface of the second patterned metal layer during the molding process. As a result, the production cost is reduced and the packaging process is simplified.

Several exemplary embodiments accompanied with figures are described in detail below to further describe the invention in details.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1A to FIG. 1F are schematic cross-sectional views illustrating a manufacturing method of a chip package structure according to an embodiment of the invention.

FIG. 2 is a schematic three-dimensional view illustrating a chip package structure according to an embodiment of the invention.

FIG. 3 is a schematic three-dimensional view illustrating the chip package structure depicted in FIG. 2 from another angle.

FIG. 4A to FIG. 4D are schematic cross-sectional views illustrating a manufacturing method of a chip package structure according to another embodiment of the invention.

DETAILED DESCRIPTION OF DISCLOSED EMBODIMENTS

FIG. 1A to FIG. 1F are schematic cross-sectional views illustrating a manufacturing method of a chip package structure according to an embodiment of the invention. According to the present embodiment, the manufacturing method of the chip package structure includes the following steps. A substrate 105 shown in FIG. 1C is provided. The substrate 105 includes a first metal layer 110a, a second metal layer 120a, and an insulation layer 130 located between the first metal layer 110a and the second metal layer 120a. To be specific, as shown in FIG. 1A to FIG. 1C, formation of the substrate 105 includes the following steps. The first metal layer 110a is provided first as shown in FIG. 1A, a connection bump 115 is formed on the first metal layer 110a as shown in FIG. 1B, and the insulation layer 130 is formed on the first metal layer 110a or on the second metal layer 120a as shown in FIG. 1C. In the present embodiment, the insulation layer 130 may be formed by coating or adherence, for instance. The first metal layer 110a and the second metal layer 120a are then laminated, as shown in FIG. 1C, such that the first metal layer 110a can be thermally coupled to the second metal layer 120a through the connection bump 115, and that the insulation layer 130 is distributed between the first metal layer 110a and the second metal layer 120a and surrounds the connection bump 115.

Certainly, in another embodiment of the invention, the connection bump 115 may be formed on the second metal layer 120a, the insulation layer 130 is formed, and then the first metal layer 110a and the second metal layer 120a are laminated to form the substrate 105. The formation of the substrate 105 is not limited to those described herein. As long as the connection bump 115 is located between the first metal layer 110a and the second metal layer 120a to ther-

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mally couple the first metal layer 110a to the second metal layer 120a, and the insulation layer 130 surrounds the connection bump 115 and is distributed between the first metal layer 110a and the second metal layer 120a, the formation of the substrate 105 does not depart from the scope of protection provided in the invention.

FIG. 2 is a schematic three-dimensional view illustrating a chip package structure according to an embodiment of the invention. Referring to FIG. 1D and FIG. 2, a first groove 116 is formed in the first metal layer 110a so as to form a first patterned metal layer 110 shown in FIG. 1D and FIG. 2. The first patterned metal layer 110 includes a chip pad 112 and a plurality of bonding pads 114, and the first groove 116 exists between each of the bonding pads 114 and the chip pad 112. That is, the first patterned metal layer 110 is separated into the chip pad 112 and the bonding pads 114 by the first groove 116. The chip pad 112 as shown in FIG. 2 includes a plurality of first recesses 112a. The first recesses 112a are located at a periphery of the chip pad 112, and the bonding pads 114 are respectively located in the first recesses 112a.

In particular, the chip pad 112 shown in FIG. 2 includes a first main body 112b and a plurality of first extensions 112c. The first main body 112b serves to carry a chip (e.g., the chip 200 shown in FIG. 1F), and the first extensions 112c extend in a direction away from the first main body 112b and collectively define the first recesses 112a with the first main body 112b. As shown in FIG. 2, each of the first extensions 112c respectively extends between every two adjacent bonding pads 114, and at least one edge of each of the first extensions 112c is aligned to at least one edge of the adjacent bonding pads 114.

FIG. 3 is a schematic three-dimensional view illustrating the chip package structure depicted in FIG. 2 from another angle. Referring to FIG. 1D and FIG. 2, similarly, a second groove 126 is formed in the second metal layer 120a so as to form a second patterned metal layer 120 as shown in FIG. 1D and FIG. 3. The second patterned metal layer 120 includes a heat dissipation block 122 and a plurality of terminal pads 124, and the second groove 126 exists between each of the terminal pads 124 and the heat dissipation block 122. That is, the second patterned metal layer 120 is separated into the heat dissipation block 122 and the terminal pads 124 by the second groove 126. The heat dissipation block 122 shown in FIG. 3 includes a plurality of second recesses 122a. The second recesses 122a are located at a periphery of the heat dissipation block 122, and the terminal pads 124 are respectively located in the second recesses 122a. The heat dissipation block 122 may be arranged corresponding to the chip pad 112 in position, and the connection bump 115 is located between the chip pad 112 and the heat dissipation block 122, as shown in FIG. 1C, so as to thermally couple the chip pad 112 to the heat dissipation block 122. The insulation layer 130 surrounds the connection bump 115 and is distributed between the bonding pads 114 and the terminal pads 124. According to the present embodiment of the invention, a size of the heat dissipation block 122 is not smaller than a size of the chip pad 112. Preferably, the size of the heat dissipation block 122 is larger than the size of the chip pad 112 in order to enhance the heat dissipation efficiency.

In particular, the heat dissipation block 122 as shown in FIG. 3 includes a second main body 122b and a plurality of second extensions 122c. The second extensions 122c extend in a direction away from the second main body 122b and collectively define the second recesses 122a with the second main body 122b. As shown in FIG. 3, each of the second

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extensions **122c** respectively extends between every two adjacent terminal pads **124**, and at least one edge of each of the second extensions **122c** is aligned to at least one edge of the adjacent terminal pads **124**.

Plural conductive vias **400** as shown in FIG. 1E are formed. The conductive vias **400** respectively penetrate the bonding pads **114** and the insulation layer **130** and are connected to the corresponding terminal pads **124** so as to electrically connect the bonding pads **114** with the terminal pads **124**. In the present embodiment, the conductive vias **400** may be formed by first forming holes respectively penetrating the bonding pads **114** and the insulation layer **130** until the terminal pads **124** are exposed, and then forming the conductive material in the holes by filling in solder materials or by electroplating. To this point, the lead frame **100** in the chip package structure of the present embodiment is substantially fabricated.

With reference to FIG. 1F and FIG. 2, a chip **200** is disposed on the chip pad **112** and is electrically connected to the bonding pads **114**. Specifically, the chip **200** is disposed on the first main body **112b** of the chip pad **112**, and the chip **200** and the bonding pads **114** may be electrically connected by a plurality of bonding wires **600** as shown in FIG. 1F. Note that only one of the bonding wires **600** is shown in FIG. 2 for clear illustration. The number of the bonding wires **600** and the number of the bonding pads **114** are not limited herein. An encapsulant **300** is then formed, which covers the first patterned metal layer **110**, the bonding wires **600** and the chip **200**, and can further fill in the first groove **116**. So far, the chip package structure **10** described in the present embodiment is substantially formed.

As shown in FIG. 1F, the chip package structure **10** that is formed according to the aforesaid manufacturing method includes the lead frame **100**, the chip **200**, and the encapsulant **300**. The lead frame **100** includes a first patterned metal layer **110**, a second patterned metal layer **120**, and an insulation layer **130**. The first patterned metal layer **110** includes a chip pad **112** and a plurality of bonding pads **114**. The chip pad **112** includes a plurality of first recesses **112a** located at a periphery of the chip pad **112**. The bonding pads **114** are respectively located in the first recesses **112a**, and a first groove **116** exists between each of the bonding pads **114** and the chip pad **112**. The second patterned metal layer **120** includes a heat dissipation block **122** and a plurality of terminal pads **124**. The heat dissipation block **122** includes a plurality of second recesses **122a** located at a periphery of the heat dissipation block **122**. The terminal pads **124** are respectively located in the second recesses **122a** and electrically connected to the corresponding bonding pads **114**. A second groove **126** exists between each of the terminal pads **124** and the heat dissipation block **122**. In the present embodiment, the connection bump **115** is located between the first patterned metal layer **110** and the second patterned metal layer **120** and connects the chip pad **112** and the heat dissipation block **122**, so as to thermally couple the chip pad **112** to the heat dissipation block **122**. The insulation layer **130** surrounds the connection bump **115** and is distributed between the bonding pads **114** and the terminal pads **124**. The chip **200** is disposed on the chip pad **112** and electrically connected to the bonding pads **114** through the bonding wires **600**, for instance. The encapsulant **300** covers the first patterned metal layer **110** and the chip **200**, and can further fill in the first groove **116**. According to the present embodiment, the size of the heat dissipation block **122** is larger than the size of the chip pad **112**, as shown in FIG. 1F, so as to enhance the heat dissipation efficiency. Thereby, a minimum horizontal distance **D1** from each of the bonding pads **114** to

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one side **210** of the chip **200** is smaller than a minimum horizontal distance **D2** from each of the corresponding terminal pads **124** to an orthogonal projection of the side **210** of the chip **200** on the heat dissipation block **122**.

In light of the above, in the chip package structure **10** of the present embodiment, the chip pad **112** and the bonding pads **114** are defined by forming the first groove **116** in the first metal layer **110a** of the substrate **105**, and the heat dissipation block **122** and the terminal pads **124** are defined by forming the second groove **126** in the second metal layer **120a** of the substrate **105**. Thus, the bonding pads **114** can extend near to the periphery of the chip **200** according to product requirements, so as to reduce the lengths of the bonding wires **600** connecting the chip **200** and the bonding pads **114**, i.e., reduce the distance of wire bonding. Thereby, the material cost can be reduced, and the yield of the wire bonding process and the subsequent processes can be improved. Besides, the dimensions of the terminal pads **124** need not be equal to the dimensions of the corresponding bonding pads **114** as long as the terminal pads **124** can be connected to the conductive vias **400** that penetrate the corresponding bonding pads **114** and the insulation layer **130**. Hence, the dimensions of the terminal pads **124** may be properly reduced according to actual product requirements so that the dimensions of the heat dissipation block **122** can be enlarged and the resultant heat dissipation area of the heat dissipation block **122** is increased. In addition, since the chip pad **112** formed according to the manufacturing method described herein extends between the adjacent bonding pads **114**, and the heat dissipation block **122** extends between the adjacent terminal pads **124**, not only the heat dissipation area is increased, but also the distance between the heat dissipation region and the electrical connection region is shortened so that the thermal impedance of the chip package structure is reduced. Moreover, since the first patterned metal layer **110** and the second patterned metal layer **120** described herein are insulated from each other by the insulation layer **130**, during the molding process, the encapsulant **300** is unable to overflow onto the bottom surface of the second patterned metal layer **120** through the first groove **116** and the second groove **126**, so that it is not necessary to adhere a tape to the bottom surface of the second patterned metal layer **120** during the molding process. As a result, the production cost is reduced, and the packaging process is simplified.

FIG. 4A to FIG. 4D are schematic cross-sectional views illustrating a manufacturing method of a chip package structure according to another embodiment of the invention. It should be mentioned that the manufacturing method of the chip package structure described in the present embodiment is similar to that provided in the previous embodiment, and therefore reference numbers and some descriptions provided in the previous exemplary embodiment are also applied in the following exemplary embodiment. The same reference numbers represent the same or similar components in these exemplary embodiments, and repetitive descriptions are omitted. The descriptions similar to the omitted parts may be found in the previous embodiments and will not be again provided hereinafter.

According to the present embodiment, the manufacturing method of the chip package structure includes following steps. Referring to FIG. 4A and FIG. 4B, the first metal layer **110a**, the insulation layer **130**, and the second metal layer **120a** are laminated to form the substrate **105** as shown in FIG. 4B. Particularly, in the present embodiment, the insulation layer **130** may first be formed on the second metal layer **120a** by coating or adherence, for instance, and the first

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metal layer **110a** is then laminated to the insulation layer **130** and the second metal layer **120a**. In another embodiment of the invention, the insulation layer **130** may be formed on the first metal layer **110a**, and the second metal layer **120a** is then laminated to the insulation layer **130** and the first metal layer **110a**. The formation of the substrate **105** is not limited in the invention. As long as the first metal layer **110a**, the insulation layer **130**, and the second metal layer **120a** are laminated to form the substrate **105**, the formation of the substrate **105** does not depart from the scope of protection provided in the invention.

The first groove **116** is formed in the first metal layer **110a** shown in FIG. 4B to form the first patterned metal layer **110** shown in FIG. 4C. In the present embodiment, the first groove **116** is formed at the location similar to that shown in FIG. 2 to separate the first metal layer **110a** into a chip pad **112** and a plurality of bonding pads **114**; that is, the first patterned metal layer **110** includes the chip pad **112** and the bonding pads **114**, and the first groove **116** exists between each bonding pad **114** and the chip pad **112**. The chip pad **112** may include a plurality of first recesses **112a**, as shown in FIG. 2. The first recesses **112a** are located at a periphery of the chip pad **112**, and the bonding pads **114** are respectively located in the first recesses **112a**.

The second groove **126** is formed in the second metal layer **120a** shown in FIG. 4B to form the second patterned metal layer **120** shown in FIG. 4C. In the present embodiment, the second groove **126** is formed at the location similar to that shown in FIG. 3 to separate the second metal layer **120a** into a heat dissipation block **122** and a plurality of terminal pads **124**; that is, the second patterned metal layer **120** includes the heat dissipation block **122** and the terminal pads **124**, and the second groove **126** exists between each terminal pad **124** and the heat dissipation block **122**. The heat dissipation block **122** includes a plurality of second recesses **122a**, as shown in FIG. 3. The second recesses **122a** are located at a periphery of the heat dissipation block **122**, and the terminal pads **124** are respectively located in the second recesses **122a**. The heat dissipation block **122** may be arranged corresponding to the chip pad **112** in position, as shown in FIG. 4C, and the size of the heat dissipation block **122** is not smaller than the size of the chip pad **112**. Preferably, the size of the heat dissipation block **122** is larger than the size of the chip pad **112** so as to expand the heat dissipation area. The insulation layer **130** is distributed between the chip pad **112** and the heat dissipation block **122** and between the bonding pads **114** and the terminal pads **124**; namely, the insulation layer **130** is evenly distributed between the first patterned metal layer **110** and the second patterned metal layer **120**.

Plural conductive vias **400** are formed as shown in FIG. 4C. The conductive vias **400** respectively penetrate the bonding pads **114** and the insulation layer **130** and are connected to the corresponding terminal pads **124** so as to electrically connect the bonding pads **114** with the terminal pads **124**. Here, the method of forming the conductive vias **400** is as described for that shown in FIG. 1E above. Besides, in the present embodiment, plural thermal vias **500** may be further formed, where the thermal vias **500** penetrate the chip pad **112** and the insulation layer **130** and are connected to the heat dissipation block **122**, as shown in FIG. 4C, so as to thermally couple the chip pad **112** to the heat dissipation block **122**. That is, the difference between the present embodiment and the previous embodiment lies in the omission of forming the connection bump **115** shown in FIG. 1B on the first metal layer **110a** or the second metal layer **120a**, but instead forming the thermal vias **500** pen-

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etrating the chip pad **112** and the insulation layer **130** to thermally couple the chip pad **112** to the heat dissipation block **122**. To this point, the lead frame **100a** in the chip package structure of the present embodiment is substantially fabricated.

Referring to FIG. 4D, the chip **200** is disposed on the chip pad **112** and is electrically connected to the bonding pads **114**. In the present embodiment, the chip **200** is electrically connected to the bonding pads **114** through a plurality of bonding wires **600**, for instance. The encapsulant **300** is then formed, which covers the first patterned metal layer **110**, the bonding wires **600** and the chip **200**, and can further fill in the first groove **116**. So far, the chip package structure **10a** described in the present embodiment is substantially formed.

Structurally, the chip package structure **10a** and the chip package structure **10** shown in FIG. 1F are similar, whereas the chip package structure **10a** described in the present embodiment does not include the connection bump **115** connecting the first patterned metal layer **110** and the second patterned metal layer **120** as shown in FIG. 1B, and the insulation layer **130** in the chip package structure **10a** is distributed evenly between the first patterned metal layer **110** and the second patterned metal layer **120**. In addition, the chip package structure **10a** further includes the thermal vias **500** which penetrate the chip pad **112** and the insulation layer **130** and are connected to the heat dissipation block **122**, so as to thermally couple the chip pad **112** to the heat dissipation block **122**. Namely, the difference between the chip package structure **10a** described herein and the chip package structure **10** shown in FIG. 1F lies in that the present embodiment uses the thermal vias **500** penetrating the chip pad **112** and the insulation layer **130** to thermally couple the chip pad **112** to the heat dissipation block **122**, but the chip package structure **10** uses the connection bump **115** connecting the chip pad **112** and the heat dissipation block **122** to thermally couple the chip pad **112** to the heat dissipation block **122**. Moreover, in the present embodiment, the dimensions of the heat dissipation block **122** is larger than the dimensions of the chip pad **112**, as shown in FIG. 4D, so as to enhance the heat dissipation efficiency. Thereby, the minimum horizontal distance D1 from each of the bonding pads **114** to one side **210** of the chip **200** is smaller than the minimum horizontal distance D2 from each of the corresponding terminal pads **124** to the orthogonal projection of the side **210** of the chip **200** on the heat dissipation block **122**.

To sum up, the lead frame of the chip package structure in the invention is formed by patterning the first metal layer of the substrate to form the first groove that separates the chip pad from the bonding pads, and patterning the second metal layer of the substrate to form the second groove that separates the heat dissipation block from the terminal pads. Thus, the bonding pads can extend near to the periphery of the chip according to product requirements, so as to reduce the distance of wire bonding. Thereby, the material cost can be reduced, and the yield of the wire bonding process and the subsequent processes can be improved. Besides, the dimensions of the terminal pads need not be equal to the dimensions of the corresponding bonding pads as long as the terminal pads can be connected to the conductive vias that penetrate the corresponding bonding pads and the insulation layer. Hence, the dimensions of the terminal pads may be properly reduced according to actual product requirements so that the dimensions of the heat dissipation block can be enlarged and the resultant heat dissipation area of the heat dissipation block is increased. In addition, since the chip pad formed according to the manufacturing method described

herein extends between the adjacent bonding pads, and the heat dissipation block extends between the adjacent terminal pads, not only the heat dissipation area is increased, but also the distance between the heat dissipation region and the electrical connection region is shortened so that the thermal impedance of the chip package structure is reduced. Moreover, the invention can use the connection bump connecting the chip pad and the heat dissipation block or the thermal vias penetrating the chip pad and the insulation layer and being connected to the heat dissipation block to form thermal coupling between the chip pad and the heat dissipation block, so as to enhance the heat dissipation effects of the chip package structure.

Moreover, since the first patterned metal layer and the second patterned metal layer described herein are insulated from each other by the insulation layer, during the molding process, the encapsulant is unable to overflow onto the bottom surface of the second patterned metal layer through the first groove and the second groove, so that it is not necessary to adhere a tape to the bottom surface of the second patterned metal layer during the molding process. As a result, the production cost is reduced, and the packaging process is simplified.

Although the invention has been described with reference to the above embodiments, it will be apparent to one of ordinary skill in the art that modifications to the described embodiments may be made without departing from the spirit of the invention. Accordingly, the scope of the invention will be defined by the attached claims and not by the above detailed descriptions.

What is claimed is:

1. A chip package structure comprising:

a lead frame comprising:

a first patterned metal layer comprising a chip pad and a plurality of bonding pads, the chip pad comprising a first main body, a plurality of first extensions and a plurality of first recesses, the first extensions extending in a direction away from the first main body, such that the first extensions and the first main body collectively define the first recesses, each of the first extensions respectively extending between every two adjacent bonding pads, and at least one edge of each of the first extensions aligned to at least one edge of the adjacent bonding pads, the first recesses being located at a periphery of the chip pad, the bonding pads being respectively located in the first recesses, and a first groove existing between each of the bonding pads and the chip pad;

a second patterned metal layer connected to the first patterned metal layer, the second patterned metal layer comprising a heat dissipation block and a plurality of terminal pads, the heat dissipation block being thermally coupled to the chip pad and comprising a plurality of second recesses, the second recesses being located at a periphery of the heat dissipation block, the terminal pads being respec-

tively located in the second recesses and electrically connected to the corresponding bonding pads, a second groove existing between each of the terminal pads and the heat dissipation block; and

an insulation layer located between the bonding pads and the terminal pads;

a chip disposed on the first main body of the chip pad and electrically connected to the bonding pads; and

an encapsulant covering the first patterned metal layer and the chip.

2. The chip package structure as recited in claim 1, further comprising a plurality of conductive vias, the conductive vias respectively penetrating the bonding pads and the insulation layer and being connected to the corresponding terminal pads respectively so as to electrically connect the bonding pads with the terminal pads.

3. The chip package structure as recited in claim 1, wherein a size of the heat dissipation block is not smaller than a size of the chip pad.

4. The chip package structure as recited in claim 1, wherein a minimum horizontal distance from each of the bonding pads to one side of the chip is smaller than a minimum horizontal distance from each of the corresponding terminal pad to an orthogonal projection of the side of the chip on the heat dissipation block.

5. The chip package structure as recited in claim 1, wherein the heat dissipation block comprises a second main body and a plurality of second extensions, the second extensions extend in a direction away from the second main body, such that the second extensions and the second main body collectively define the second recesses, each of the second extensions respectively extends between every two adjacent terminal pads, and at least one edge of each of the second extensions is aligned to at least one edge of the adjacent terminal pads.

6. The chip package structure as recited in claim 1, further comprising a connection bump located between the first patterned metal layer and the second patterned metal layer, the connection bump connecting the chip pad and the heat dissipation block, so as to thermally couple the chip pad to the heat dissipation block.

7. The chip package structure as recited in claim 6, wherein the insulation layer surrounds the connection bump and is distributed between the bonding pads and the terminal pads.

8. The chip package structure as recited in claim 1, wherein the insulation layer is distributed between the chip pad and the heat dissipation block and between the bonding pads and the terminal pads.

9. The chip package structure as recited in claim 8, further comprising a plurality of thermal vias, the thermal vias penetrating the chip pad and the insulation layer and being connected to the heat dissipation block, so as to thermally couple the chip pad to the heat dissipation block.

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